

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE



Applicants: Constantin Bulucea and Rebecca Rossen
 Assignee: Siliconix incorporated
 Title: TRENCH DMOS POWER TRANSISTOR WITH FIELD-SHAPING BODY PROFILE AND THREE-DIMENSIONAL GEOMETRY
 Serial No.: 08/453,285 Filed: 5/30/95
 Examiner: J. Carroll Group Art Unit: 2508
 Attorney Docket No.: M-799-3C US

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 10-21-96
 San Jose, California
 September 30, 1996

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Sir:

In response to the Office Action of April 4, 1996, please amend the above-referenced patent application as follows:

IN THE CLAIMS

Please cancel Claims 45 and 66.

In Claim 42, at line 9, please delete "second" and substitute --first--.

In Claim 63, at line 9, please delete "second" and substitute --first--.

In Claim 64, at line 1, please delete "32" and substitute --54--.

Please amend Claims 30, 54, 56 and 58 as follows:

Detl F3
 30. (Twice amended) A trench DMOS transistor cell, comprising:

a substrate of semiconductor material of a first electrical conductivity type having a top surface;

a first covering layer of semiconductor material of said first electrical conductivity type, said first covering layer (i) having a dopant concentration less than that of said substrate, (ii) having a top surface and (iii) being contiguous to and overlying the substrate top surface;

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